

VMDSEMI

**VUDA002R37ANA**

**Datasheet**

## General Description

$V_{(BR)DSS}$	$R_{DS(ON)_{max}}$	$I_D$
20V	370mΩ@4.5V	0.75A
	480mΩ@2.5V	
	620mΩ@1.8V	

## Symbol

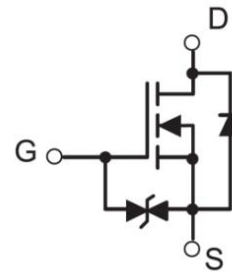


Figure 1 Symbol of VUDA002R37ANA

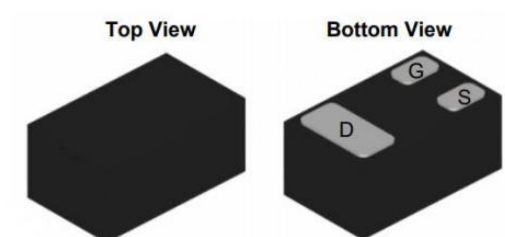
## Features

- Lead Free Product is Acquired
- Surface Mount Package
- Operated at Low Logic Level Gate Drive

## Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

## Package Type



### DFN1006-3L

Figure 2 Package Type of VUDA002R37ANA

## Ordering Information

Product Name	Package
VUDA002R37ANA	DFN1006-3L

**Absolute Maximum Ratings** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V
Continuous Drain Current	$I_D$	0.75	A
Pulsed Drain Current ( $t_p=10\mu\text{s}$ )	$I_{DM}$	1.8	A
Total Power Dissipation <sup>Note1</sup>	$P_D$	100	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 to 150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	$T_L$	260	$^\circ\text{C}$

**Thermal Resistance**

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient <sup>Note1</sup>	$R_{\theta JA}$		125		$^\circ\text{C}/\text{W}$

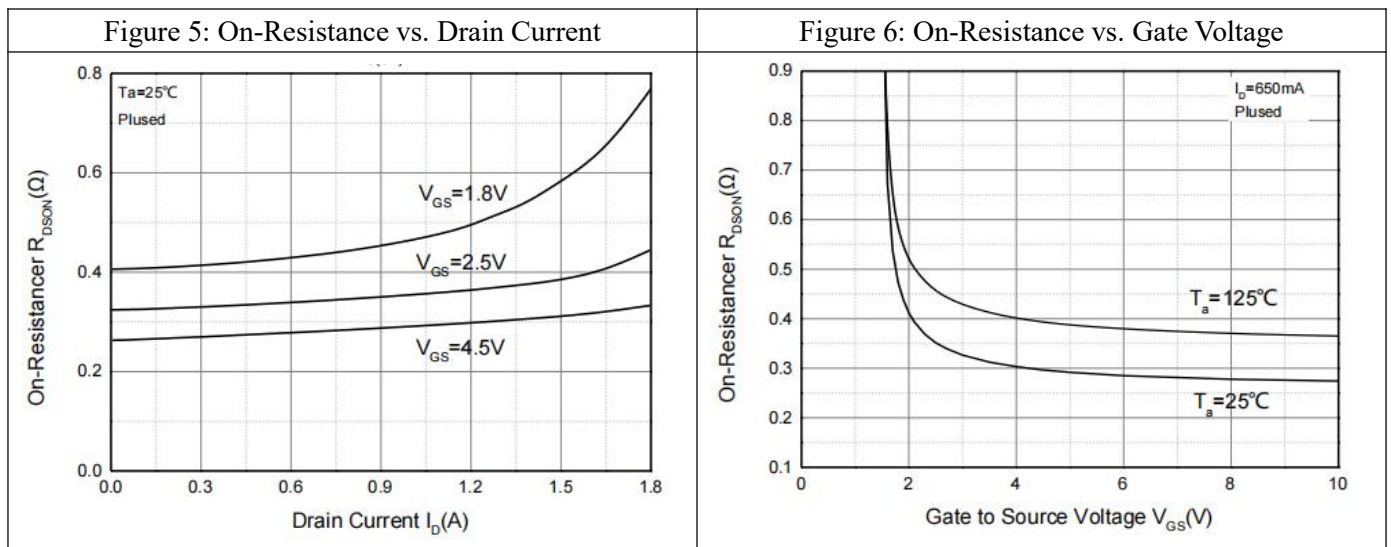
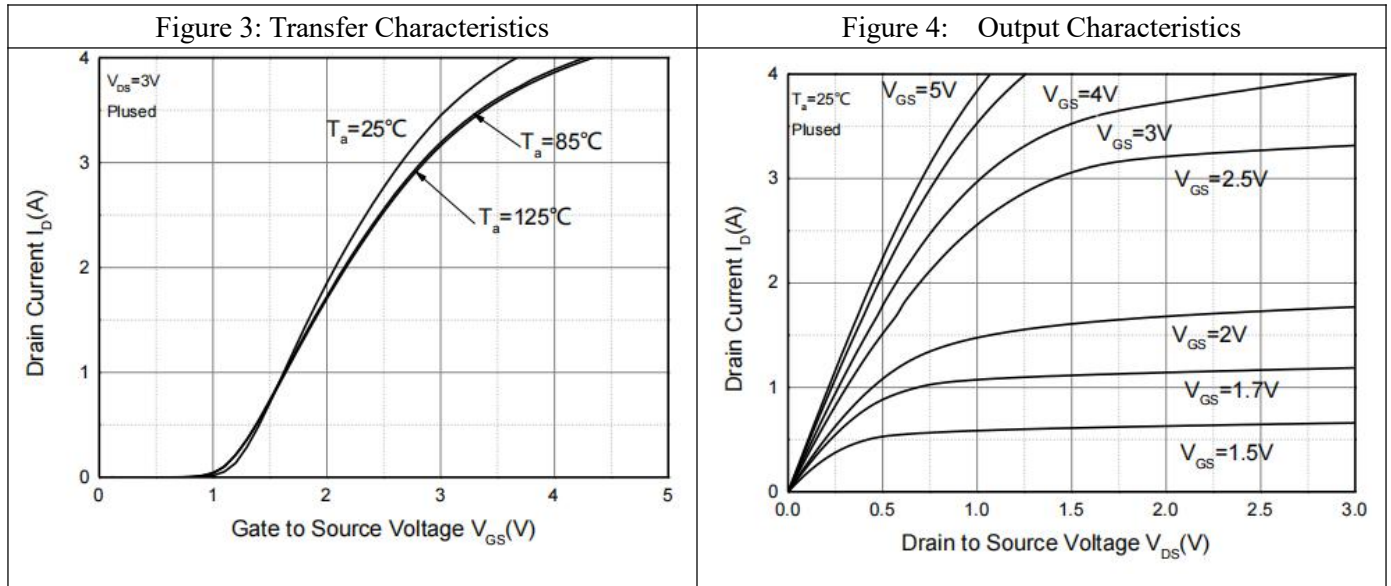
**Electrical Characteristics** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified)

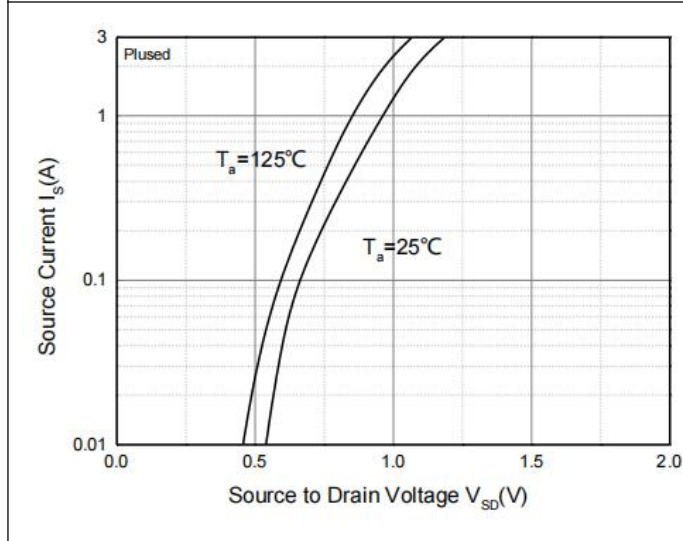
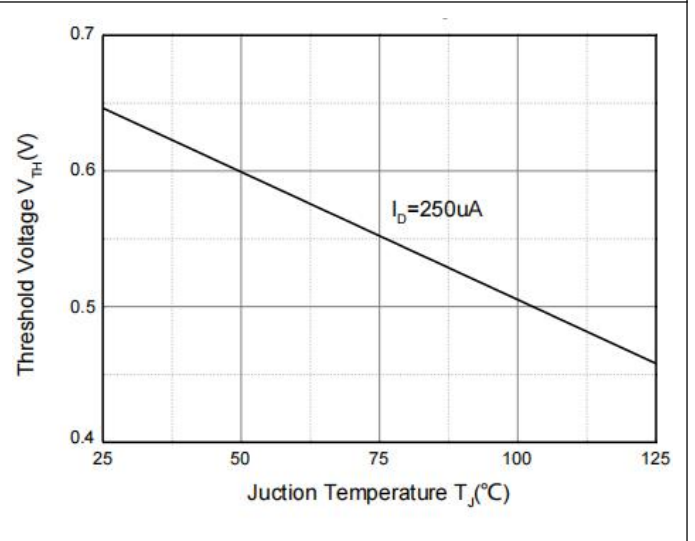
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Statistic Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 10V, V_{DS}=0V$			$\pm 20$	$\mu A$
Gate Threshold Voltage <sup>Note2</sup>	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.35	0.75	1.0	V
Static Drain-Source On-Resistance <sup>Note2</sup>	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.15A$		270	370	mΩ
		$V_{GS}=2.5V, I_D=0.15A$		320	480	
		$V_{GS}=1.8V, I_D=0.15A$		415	620	
Forward tranconductance	$g_{FS}$	$V_{DS}=10V, I_D=0.15A$	15			S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=16V$		79		pF
Output Capacitance	$C_{OSS}$	$V_{GS}=0V$		13		pF
Reverse Transfer Capacitance	$C_{RSS}$	$f=1MHz$		9		pF
<b>Switching Parameters</b>						
Turn-on Delay Time <sup>Note3</sup>	$t_{d(on)}$	$V_{DS}=10V$		6.7		ns
Turn-on Rise Time <sup>Note3</sup>	$t_r$	$V_{GS}=4.5V$		4.8		
Turn-off Delay Time <sup>Note3</sup>	$t_{d(off)}$	$I_D=0.5A$		17.3		
Turn-off Fall Time <sup>Note3</sup>	$t_f$	$R_G=10\Omega$		7.4		
<b>Diode Characteristics</b>						
Diode Forward Voltage <sup>Note2</sup>	$V_{SD}$	$V_{GS}=0V, I_S=0.15A$			1.2	V

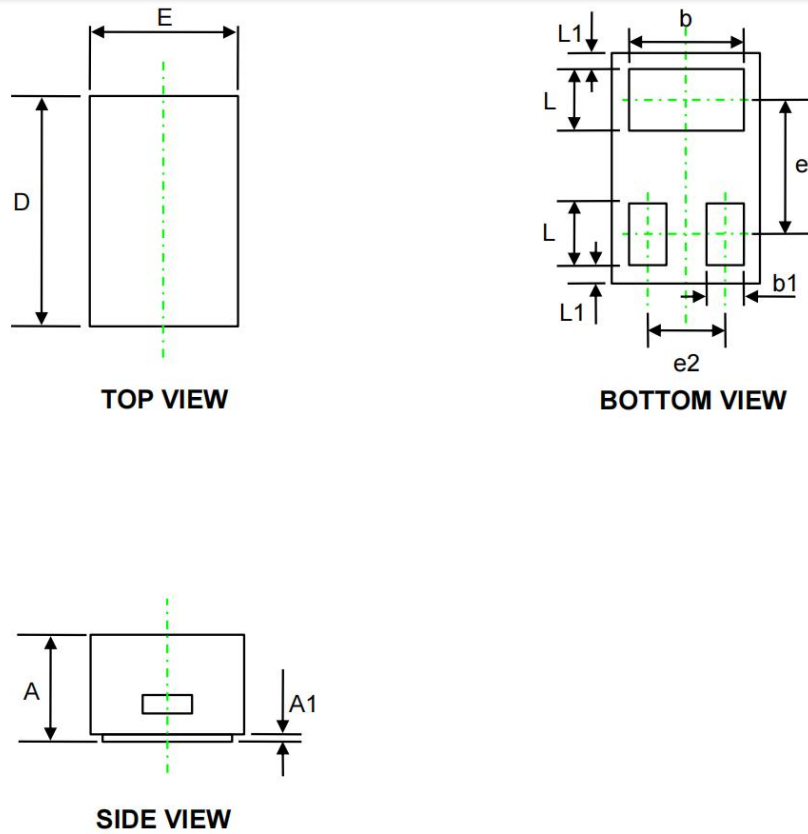
Notes :

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300 $\mu s$ , Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.

## Typical Performance Characteristics



**Figure 7: Body Diode Characteristics**

**Figure 8: Threshold Voltage**


**Mechanical Dimensions:**
**DFN1006-3L Package Information**


Symbol	Dimensions In Millimeters (mm)		
	Min.	Typ.	Max.
A	0.34	0.37	0.40
A1	0.00	0.03	0.05
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b	0.45	0.50	0.55
e	-	0.65	-
e2	-	0.35	-
L1	0.05 REF.		
L	0.20	0.25	0.30
b1	0.10	0.15	0.20

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